NPN general purpose transistors BC846W; BC847W

FEATURES

- Low current (max. 100 mA)
- Low voltage (max. 65 V).

APPLICATIONS

- General purpose switching and amplification.

DESCRIPTION

NPN transistor in a SC70; SOT323 plastic package.
PNP complements: BC856W and BC857W.

MARKING

TYPE NUMBER	MARKING CODE(1)	TYPE NUMBER	MARKING CODE(1)
BC846W	1D*	BC847AW	1E*
BC846AW	1A*	BC847BW	1F*
BC846BW	1B*	BC847CW	1G*
BC847W	1H*		

Note

1. * = - : Made in Hong Kong.
   * = t : Made in Malaysia.

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector

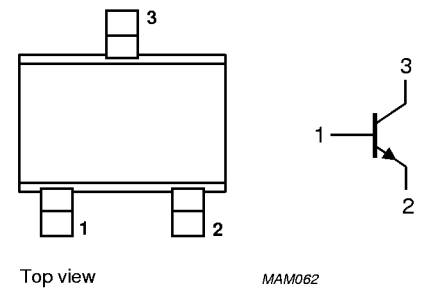


Fig.1 Simplified outline (SC70; SOT323) and symbol.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter			
	BC846W		–	80	V
	BC847W		–	50	V
V_{CEO}	collector-emitter voltage	open base			
	BC846W		–	65	V
	BC847W		–	45	V
V_{EBO}	emitter-base voltage	open collector	–	5	V
I_C	collector current (DC)		–	100	mA
I_{CM}	peak collector current		–	200	mA
I_{BM}	peak base current		–	200	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C; note 1	–	200	mW
T_{stg}	storage temperature		−65	+150	°C
T_j	junction temperature		–	150	°C
T_{amb}	operating ambient temperature		−65	+150	°C

Note

1. Transistor mounted on an FR4 printed-circuit board.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j\text{-}a}$	thermal resistance from junction to ambient	note 1	625	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

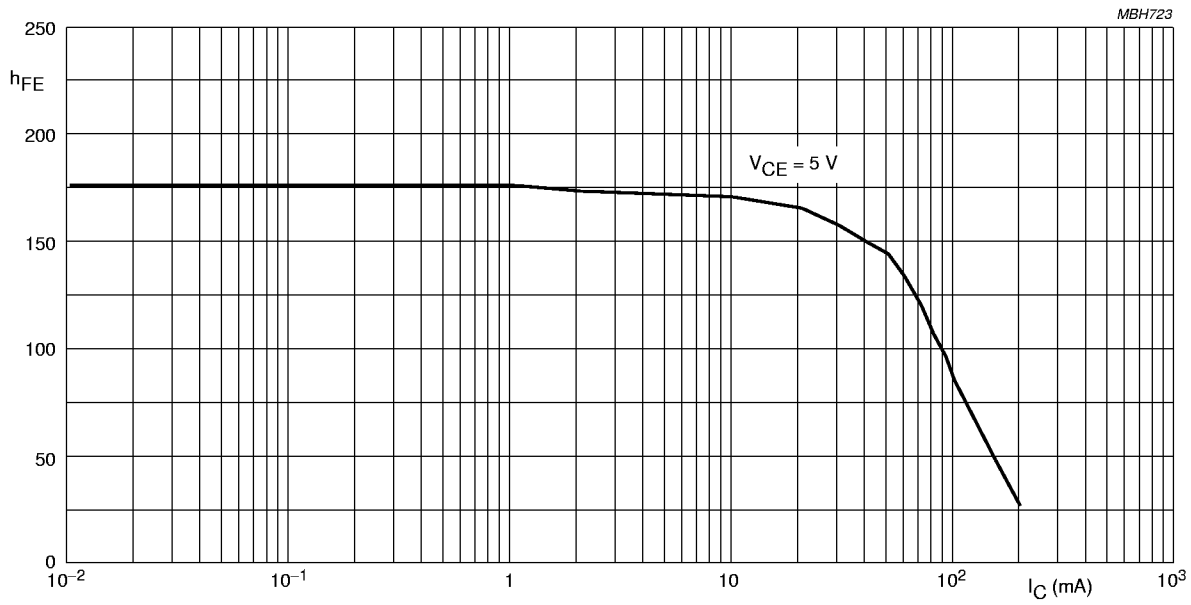
CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	collector cut-off current	I_E = 0; V_{CB} = 30 V	–	–	15	nA
		I_E = 0; V_{CB} = 30 V; T_j = 150 °C	–	–	5	µA
I_{EBO}	emitter cut-off current	I_C = 0; V_{EB} = 5 V	–	–	100	nA
h_{FE}	DC current gain	I_C = 2 mA; V_{CE} = 5 V; see Figs 2, 3 and 4				
	BC846W		110	–	450	
	BC847W		110	–	800	
	BC846AW; BC847AW		110	–	220	
	BC846BW; BC847BW		200	–	450	
	BC847CW		420	–	800	
V_{CEsat}	collector-emitter saturation voltage	I_C = 10 mA; I_B = 0.5 mA	–	–	250	mV
		I_C = 100 mA; I_B = 5 mA; note 1	–	–	600	mV
V_{BEsat}	base-emitter saturation voltage	I_C = 10 mA; I_B = 0.5 mA	–	700	–	mV
		I_C = 100 mA; I_B = 5 mA	–	900	–	mV
V_{BE}	base-emitter voltage	I_C = 2 mA; V_{CE} = 5 V	580	–	700	mV
		I_C = 10 mA; V_{CE} = 5 V	–	–	770	mV
C_c	collector capacitance	$I_E = i_e$ = 0; V_{CB} = 10 V; f = 1 MHz	–	–	3	pF
f_T	transition frequency	I_C = 10 mA; V_{CE} = 5 V; f = 100 MHz	100	–	–	MHz
F	noise figure	I_C = 200 µA; V_{CE} = 5 V; R_S = 2 kΩ; f = 1 kHz; B = 200 Hz	–	–	10	dB

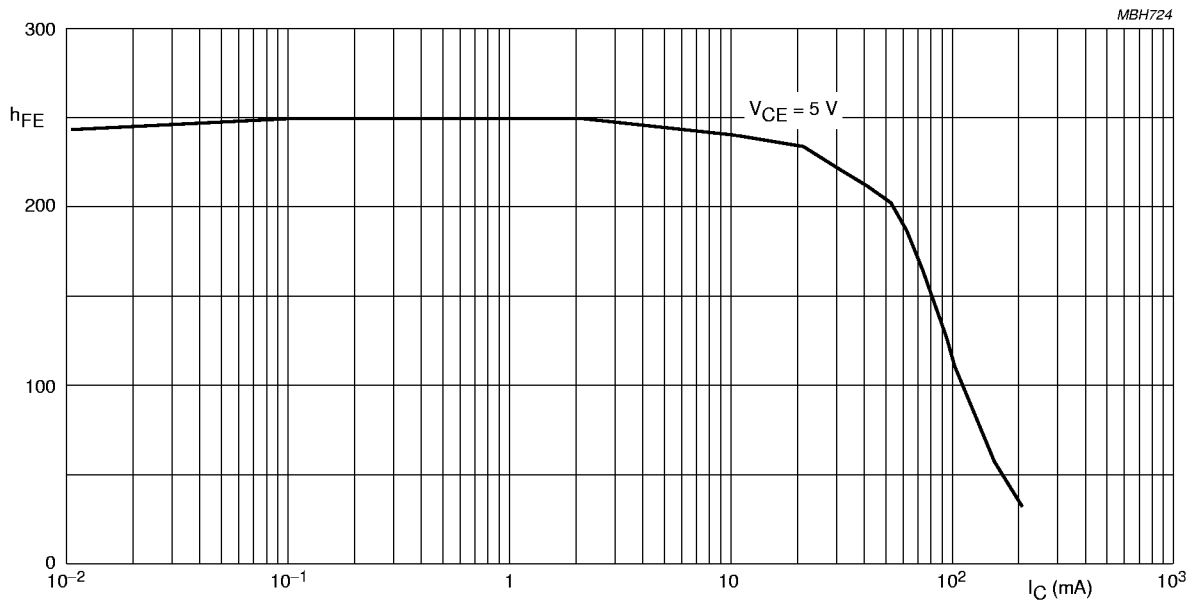
Note

1. Pulse test: $t_p \leq 300$ µs; $\delta \leq 0.02$.



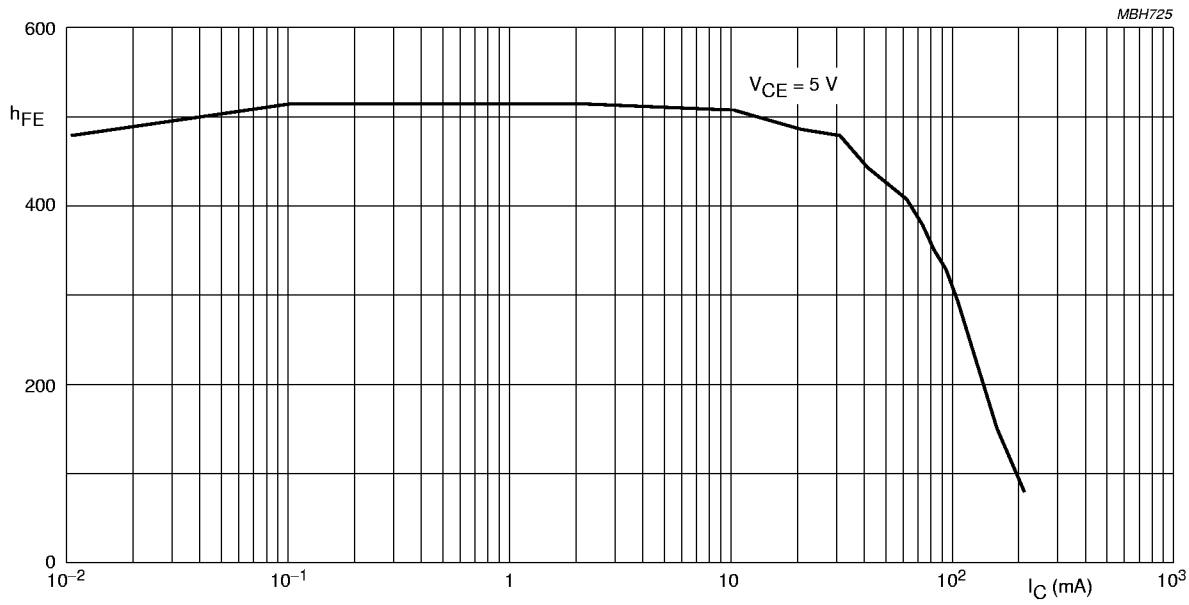
BC846AW; BC847AW.

Fig.2 DC current gain; typical values.



BC846BW; BC847BW.

Fig.3 DC current gain; typical values.

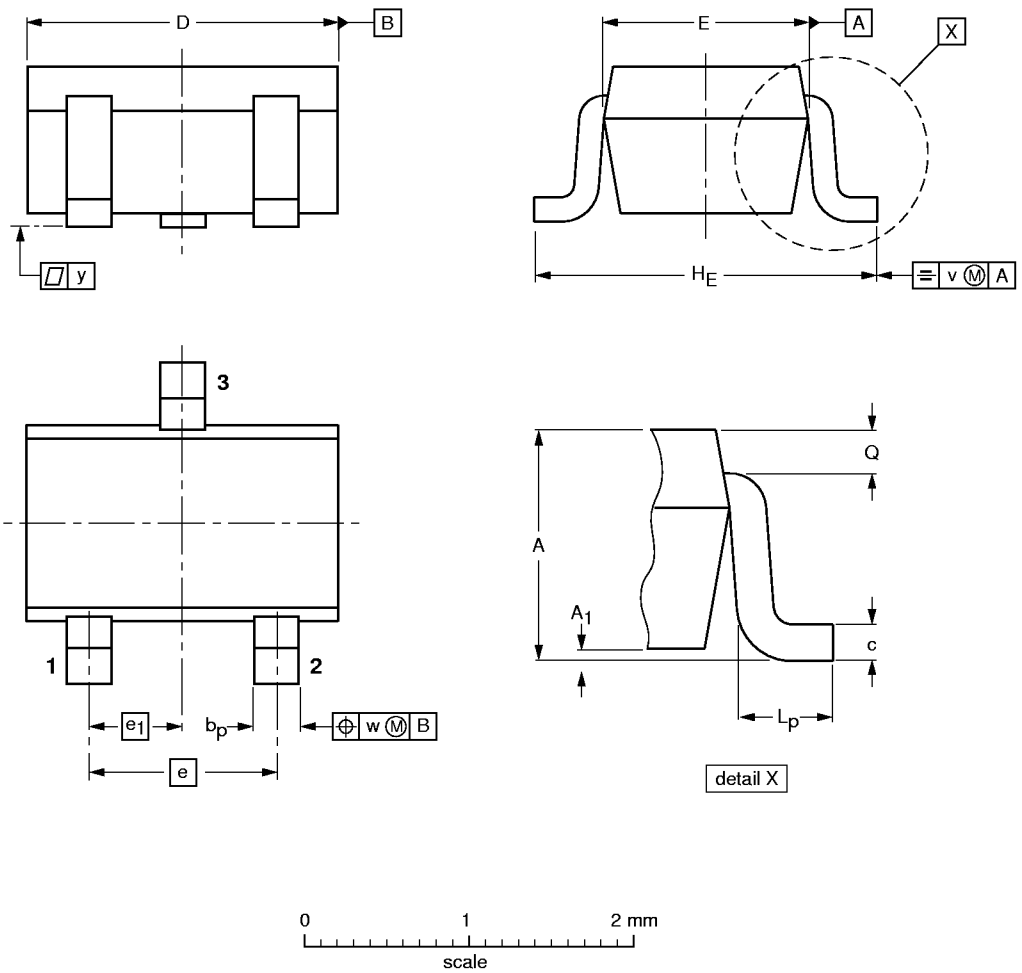


BC847CW.

Fig.4 DC current gain; typical values.

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads **SOT323**



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1 max	b_p	c	D	E	e	e_1	H_E	L_p	Q	v	w
mm	1.1 0.8	0.1	0.4 0.3	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.23 0.13	0.2	0.2

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT323			SC-70			97-02-28